

In the Specification

Please replace the paragraph beginning at page 52, line 8, with the following paragraph:

B²

-- For clarifying the structure of the carbonaceous thin film formed on the ground silicon substrate, mass spectroscopic analysis was carried out in accordance with the Laser-Desorption-Ionization Time-of-Flight method. For measurement, a Thermoquest Vision 2000 TOF-MS monitor was used. The laser used for ablation was a nitrogen laser. Before measurement, a silicon substrate was cut to a size of 5 mm and set on a target of the TOF-MS monitor. For measurement, a pulse laser was directly illuminated on the surface of the carbonaceous thin film for excitation, desorption and ionization. Positive ions were used for measurement. Figs.43 to 45 show the spectrum with increased laser strength. However, the laser power in Fig.44 is not so strong as to vary the election valence state of carbon. As may be seen from Fig.44, a cluster up to 20 carbon atoms is ascribable to a continuous peak of the difference corresponding to a carbon atom and mainly to a component in the valency state of sp³. In Fig.45, a cluster up to approximately 30 carbon atoms is mainly ascribable to a component in the valency state of sp³. If the laser power is increased further, a continuous peak with a difference of C₂ from 50 to approximately 150 carbon atoms is observed. This is the peak proper to the carbon having the graphitic structure of sp². It is seen from these that the carbonaceous thin film has a structure of an extremely small graphite in the random sp³ carbon. --

In the Claims

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Please cancel claim 18, without prejudice.

Please amend claims 12, 15, 17, and 20-23 as follows:

12. (amended) A method for manufacturing a carbonaceous complex structure comprising:

B³
Sub C¹

a step of forming a carbonaceous thin film on a smooth surface of a substrate and
a step of forming a fullerene thin film on said thus formed carbonaceous thin film.